

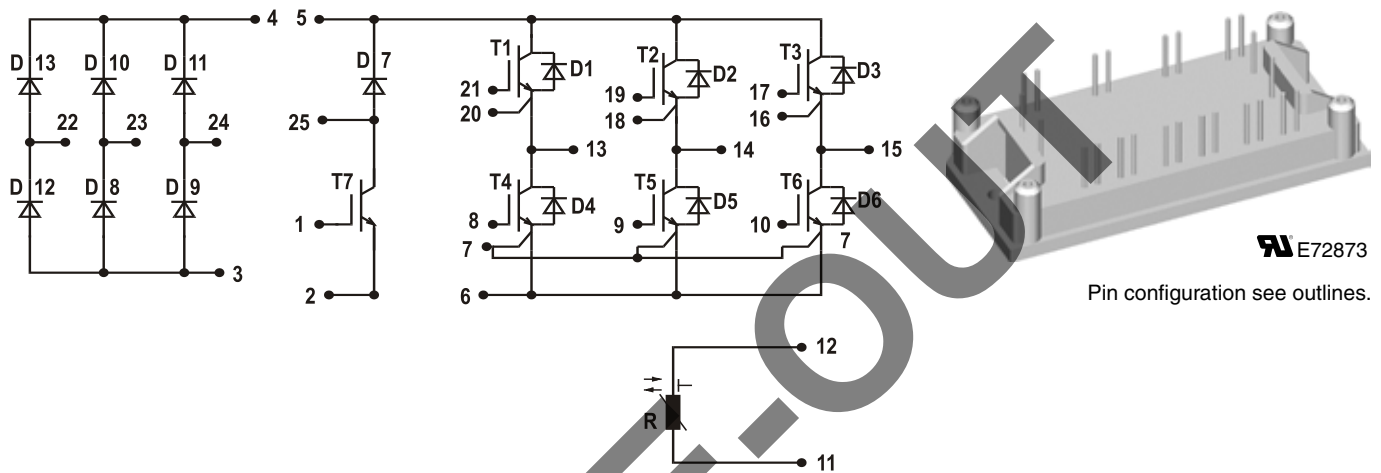
Converter - Brake - Inverter Module (CBI 1) NPT IGBT

Three Phase Rectifier	Brake Chopper	Three Phase Inverter
$V_{RRM} = 1600 \text{ V}$	$V_{CES} = 600 \text{ V}$	$V_{CES} = 600 \text{ V}$
$I_{DAVM25} = 95 \text{ A}$	$I_{C25} = 12 \text{ A}$	$I_{C25} = 25 \text{ A}$
$I_{FSM} = 250 \text{ A}$	$V_{CE(sat)} = 2.25 \text{ V}$	$V_{CE(sat)} = 2.0 \text{ V}$

Preliminary data

Part name (Marking on product)

MUBW20-06A6K



Features:

- High level of integration - only one power semiconductor module required for the whole drive
- Inverter with NPT IGBTs
 - low saturation voltage
 - positive temperature coefficient
 - fast switching
 - short tail current
- Epitaxial free wheeling diodes with hiperfast and soft reverse recovery
- Industry standard package with insulated copper base plate and soldering pins for PCB mounting
- Temperature sense included

Application:

- AC motor drives with
- Input from single or three phase grid
 - Three phase synchronous or asynchronous motor
 - Electric braking operation

Package:

- UL registered
- Industry standard E1-pack

Output Inverter T1 - T6

Symbol	Definitions	Conditions	min.	Ratings		
				typ.	max.	Unit
V_{CES}	collector emitter voltage	$T_{VJ} = 25^{\circ}\text{C}$ to 150°C			600	V
V_{GES}	max. DC gate voltage	continuous			± 20	V
V_{GEM}	max. transient collector gate voltage	transient			± 30	V
I_{C25}	collector current	$T_C = 25^{\circ}\text{C}$			25	A
I_{C80}		$T_C = 80^{\circ}\text{C}$			17	A
P_{tot}	total power dissipation	$T_C = 25^{\circ}\text{C}$			85	W
$V_{CE(sat)}$	collector emitter saturation voltage	$I_C = 15\text{ A}; V_{GE} = 15\text{ V}$		$T_{VJ} = 25^{\circ}\text{C}$ $T_{VJ} = 125^{\circ}\text{C}$	2.0 2.3	V V
$V_{GE(th)}$	gate emitter threshold voltage	$I_C = 0.4\text{ mA}; V_{GE} = V_{CE}$	$T_{VJ} = 25^{\circ}\text{C}$	4.5	6.5	V
I_{CES}	collector emitter leakage current	$V_{CE} = V_{CES}; V_{GE} = 0\text{ V}$	$T_{VJ} = 25^{\circ}\text{C}$ $T_{VJ} = 125^{\circ}\text{C}$	1.3	0.6	mA mA
I_{GES}	gate emitter leakage current	$V_{CE} = 0\text{ V}; V_{GE} = \pm 20\text{ V}$			100	nA
C_{ies}	input capacitance	$V_{CE} = 25\text{ V}; V_{GE} = 0\text{ V}; f = 1\text{ MHz}$		800		pF
$Q_{G(on)}$	total gate charge	$V_{CE} = 300\text{ V}; V_{GE} = 15\text{ V}; I_C = 15\text{ A}$		57		nC
$t_{d(on)}$	turn-on delay time	inductive load $V_{CE} = 300\text{ V}; I_C = 15\text{ A}$ $V_{GE} = \pm 15\text{ V}; R_{G(on)} = 39\ \Omega$ $R_{G(off)} = 22\ \Omega$	$T_{VJ} = 125^{\circ}\text{C}$	30		ns
t_r	current rise time			25		ns
$t_{d(off)}$	turn-off delay time			160		ns
t_f	current fall time			50		ns
E_{on}	turn-on energy per pulse			0.42		mJ
E_{off}	turn-off energy per pulse			0.44		mJ
I_{CM}	reverse bias safe operating area	RBSOA; $V_{GE} = \pm 15\text{ V}; R_G = 68\ \Omega$ $L = 100\ \mu\text{H}$; clamped induct. load $V_{CEmax} = V_{CES} - L_S \cdot di/dt$	$T_{VJ} = 125^{\circ}\text{C}$	30		A
t_{SC} (SCSOA)	short circuit safe operating area	$V_{CE} = 600\text{ V}; V_{GE} = \pm 15\text{ V};$ $R_G = 68\ \Omega$; non-repetitive	$T_{VJ} = 125^{\circ}\text{C}$	10		μs
R_{thJC}	thermal resistance junction to case	(per IGBT)			1.5	K/W
R_{thCH}	thermal resistance case to heatsink	(per IGBT)		0.55		K/W

Output Inverter D1 - D6

Symbol	Definitions	Conditions	min.	Ratings		
				typ.	max.	Unit
V_{RRM}	max. repetitive reverse voltage	$T_{VJ} = 150^{\circ}\text{C}$			600	V
I_{F25}	forward current	$T_C = 25^{\circ}\text{C}$			36	A
I_{F80}		$T_C = 80^{\circ}\text{C}$			24	A
V_F	forward voltage	$I_F = 15\text{ A}; V_{GE} = 0\text{ V}$	$T_{VJ} = 25^{\circ}\text{C}$ $T_{VJ} = 125^{\circ}\text{C}$	1.5	2.1	V V
I_{RM}	max. reverse recovery current	$V_R = 300\text{ V}$ $di_F/dt = -400\text{ A}/\mu\text{s}$ $I_F = 15\text{ A}; V_{GE} = 0\text{ V}$	$T_{VJ} = 100^{\circ}\text{C}$	14		A
t_{rr}	reverse recovery time			80		ns
$E_{rec(off)}$	reverse recovery energy			tbd		μJ
R_{thJC}	thermal resistance junction to case	(per diode)			1.6	K/W
R_{thCH}	thermal resistance case to heatsink	(per diode)		0.55		K/W

 $T_C = 25^{\circ}\text{C}$ unless otherwise stated

Brake Chopper T7

				Ratings			
Symbol	Definitions	Conditions	min.	typ.	max.	Unit	
V_{CES}	collector emitter voltage	$T_{VJ} = 25^{\circ}\text{C}$ to 150°C			600	V	
V_{GES}	max. DC gate voltage	continuous			± 20	V	
V_{GEM}	max. transient collector gate voltage	transient			± 30	V	
I_{C25}	collector current	$T_C = 25^{\circ}\text{C}$			11	A	
I_{C80}		$T_C = 80^{\circ}\text{C}$			8	A	
P_{tot}	total power dissipation	$T_C = 25^{\circ}\text{C}$			50	W	
$V_{CE(sat)}$	collector emitter saturation voltage	$I_C = 10\text{ A}$; $V_{GE} = 15\text{ V}$	$T_{VJ} = 25^{\circ}\text{C}$ $T_{VJ} = 125^{\circ}\text{C}$	2.65 3.1	3.3	V V	
$V_{GE(th)}$	gate emitter threshold voltage	$I_C = 0.2\text{ mA}$; $V_{GE} = V_{CE}$	$T_{VJ} = 25^{\circ}\text{C}$	4.5	6.5	V	
I_{CES}	collector emitter leakage current	$V_{CE} = V_{CES}$; $V_{GE} = 0\text{ V}$	$T_{VJ} = 25^{\circ}\text{C}$ $T_{VJ} = 125^{\circ}\text{C}$	0.7	0.1	mA mA	
I_{GES}	gate emitter leakage current	$V_{CE} = 0\text{ V}$; $V_{GE} = \pm 20\text{ V}$			120	nA	
C_{ies}	input capacitance	$V_{CE} = 25\text{ V}$; $V_{GE} = 0\text{ V}$; $f = 1\text{ MHz}$		220		pF	
$Q_{G(on)}$	total gate charge	$V_{CE} = 300\text{ V}$; $V_{GE} = 15\text{ V}$; $I_C = 6\text{ A}$		32		nC	
$t_{d(on)}$	turn-on delay time	inductive load $V_{CE} = 300\text{ V}$; $I_C = 8\text{ A}$ $V_{GE} = \pm 15\text{ V}$; $R_{G(on)} = 54\ \Omega$ $R_{G(off)} = 22\ \Omega$	$T_{VJ} = 125^{\circ}\text{C}$	20		ns	
t_r	current rise time			10		ns	
$t_{d(off)}$	turn-off delay time			110		ns	
t_f	current fall time			30		ns	
E_{on}	turn-on energy per pulse			0.21		mJ	
E_{off}	turn-off energy per pulse			0.26		mJ	
I_{CM}	reverse bias safe operating area	RBSOA; $V_{GE} = \pm 15\text{ V}$; $R_G = 54\ \Omega$ $L = 100\ \mu\text{H}$; clamped induct. load $V_{CEmax} = V_{CES} - L_S \cdot di/dt$	$T_{VJ} = 125^{\circ}\text{C}$	18		A	
t_{SC} (SCSOA)	short circuit safe operating area	$V_{CE} = 600\text{ V}$; $V_{GE} = \pm 15\text{ V}$; $R_G = 54\ \Omega$; non-repetitive	$T_{VJ} = 125^{\circ}\text{C}$	10		μs	
R_{thJC}	thermal resistance junction to case	(per IGBT)			2.75	K/W	
R_{thCH}	thermal resistance case to heatsink	(per IGBT)		0.9		K/W	

Brake Chopper D7

					Ratings			
Symbol	Definitions	Conditions	min.	typ.	max.	Unit		
V_{RRM}	<i>max. repetitive reverse voltage</i>	$T_{VJ} = 150^{\circ}\text{C}$			600	V		
I_{F25}	<i>forward current</i>	$T_C = 25^{\circ}\text{C}$			21	A		
I_{F80}		$T_C = 80^{\circ}\text{C}$			14	A		
V_F	<i>forward voltage</i>	$I_F = 10\text{ A}; V_{GE} = 0\text{ V}$	$T_{VJ} = 25^{\circ}\text{C}$ $T_{VJ} = 125^{\circ}\text{C}$	1.25	2.1	V V		
I_R	<i>reverse current</i>	$V_R = V_{RRM}$	$T_{VJ} = 25^{\circ}\text{C}$ $T_{VJ} = 125^{\circ}\text{C}$	0.2	0.06	mA mA		
I_{RM}	<i>max. reverse recovery current</i>	$V_R = 100\text{ V}; I_F = 12\text{ A}$ $di_F/dt = -100\text{ A}/\mu\text{s}$	$T_{VJ} = 100^{\circ}\text{C}$	3.5		A		
t_{rr}	<i>reverse recovery time</i>			80		ns		
R_{thJC}	<i>thermal resistance junction to case</i>	(per diode)			2.5	K/W		
R_{thCH}	<i>thermal resistance case to heatsink</i>	(per diode)		0.85		K/W		

 $T_C = 25^{\circ}\text{C}$ unless otherwise stated

Input Rectifier Bridge D8 - D13

Symbol	Definitions	Conditions	Maximum Ratings	
V_{RRM}	max. repetitive reverse voltage		1600	V
I_{FAV}	average forward current	sine 180°	$T_C = 80^\circ\text{C}$	23 A
I_{DAVM}	max. average DC output current	rectangular; $d = 1/3$; bridge	$T_C = 80^\circ\text{C}$	65 A
I_{FSM}	max. surge forward current	$t = 10\text{ ms}$; sine 50 Hz	$T_C = 25^\circ\text{C}$	250 A
P_{tot}	total power dissipation	$T_C = 25^\circ\text{C}$	65	W

Symbol	Conditions	Characteristic Values			
		min.	typ.	max.	
V _F	forward voltage	I _F = 30 A	T _{VJ} = 25°C T _{VJ} = 125°C	1.1 1.2	V V
I _R	reverse current	V _R = V _{RRM}	T _{VJ} = 25°C T _{VJ} = 125°C	0.4	0.02 mA mA
R _{thJC}	thermal resistance junction to case	(per diode)	T _{VJ} = 25°C		1.9 K/W
R _{thCH}	thermal resistance case to heatsink	(per diode)		0.65	K/W

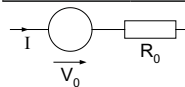
Temperature Sensor NTC

Symbol	Definitions	Conditions	Ratings		
			min.	typ.	max.
R_{25}	resistance	$T_C = 25^\circ\text{C}$	4.45	4.7	5.0
$B_{25/85}$				3510	K

Module

Symbol	Definitions	Conditions	Ratings		
			min.	typ.	max.
T_{VJ}	operating temperature		-40		125 °C
T_{VJM}	max. virtual junction temperature				150 °C
T_{stg}	storage temperature		-40		125 °C
V_{ISOL}	isolation voltage	$I_{ISOL} \leq 1\text{ mA}$; 50/60 Hz			2500 V~
M_d	mounting torque	(M4)	2.0		2.2 Nm
d_S	creep distance on surface		12.7		mm
d_A	strike distance through air		12.7		mm
Weight				40	g

Equivalent Circuits for Simulation

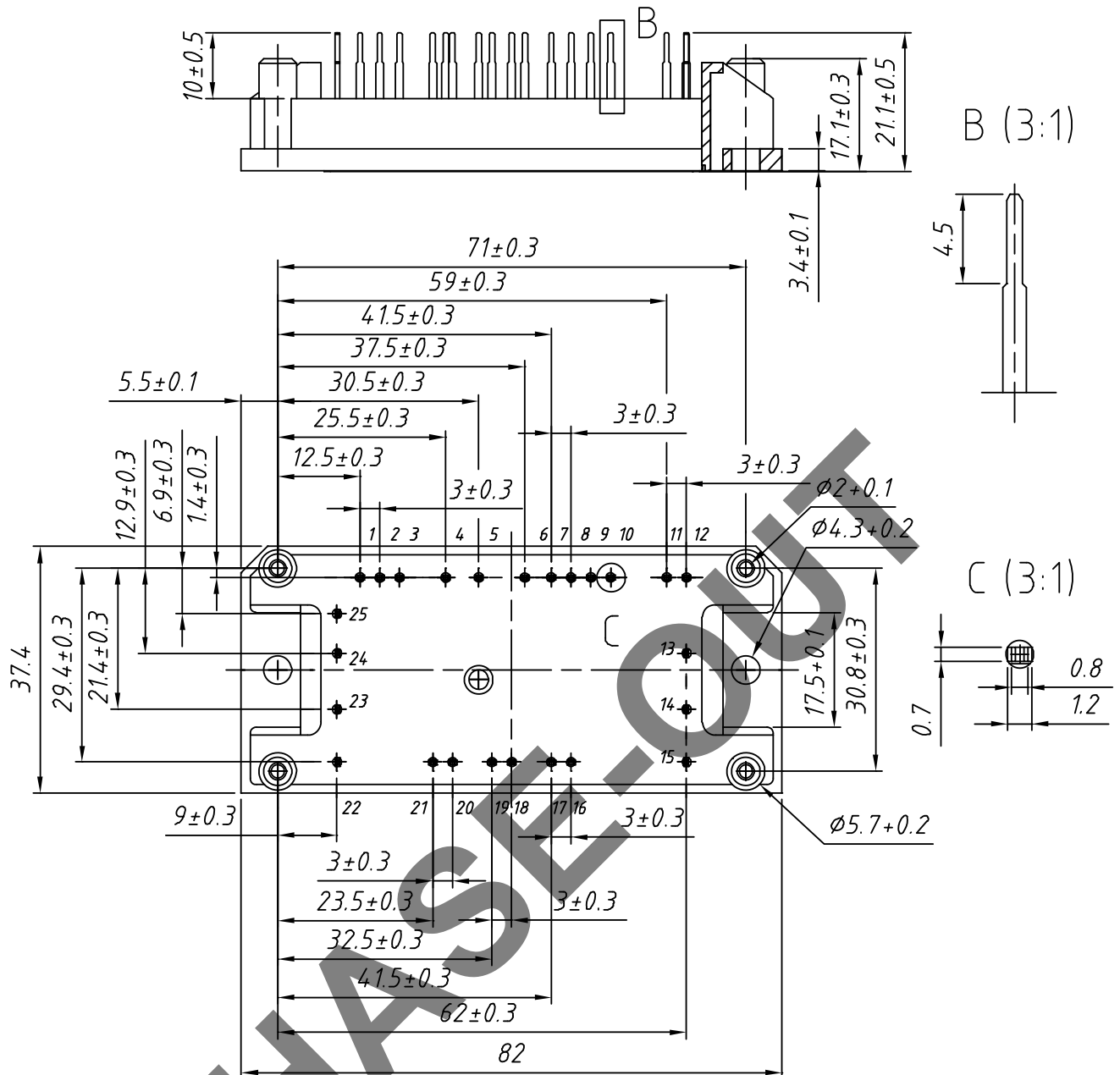


Symbol	Definitions	Conditions	Ratings		
			min.	typ.	max.
V_0	rectifier diode	D8 - D13	$T_{VJ} = 125^\circ\text{C}$	0.90	V
R_0				12	mΩ
V_0	IGBT	T1 - T6	$T_{VJ} = 125^\circ\text{C}$	1.0	V
R_0				70	mΩ
V_0	free wheeling diode	D1 - D6	$T_{VJ} = 125^\circ\text{C}$	1.25	V
R_0				13	mΩ
V_0	IGBT	T7	$T_{VJ} = 125^\circ\text{C}$	1.4	V
R_0				150	mΩ
V_0	free wheeling diode	D7	$T_{VJ} = 125^\circ\text{C}$	1.25	V
R_0				26	mΩ

$T_C = 25^\circ\text{C}$ unless otherwise stated

Outline Drawing

Dimensions in mm (1 mm = 0.0394")



Product Marking

Ordering	Part Name	Marking on Product	Delivering Mode	Base Qty	Ordering Code
Standard	MUBW 20-06A6K	MUBW20-06A6K	Box	10	500 103

Mouser Electronics

Authorized Distributor

Click to View Pricing, Inventory, Delivery & Lifecycle Information:

[IXYS:](#)

[MUBW20-06A6K](#)